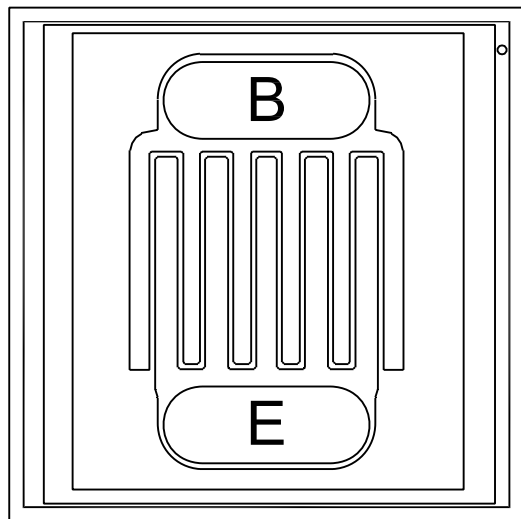


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	29 x 29 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	11.8 x 4.5 MILS
Emitter Bonding Pad Area	11.8 x 4.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au-As - 13,000Å

GEOMETRY



BACKSIDE COLLECTOR R0

GROSS DIE PER 4 INCH WAFER

13,192

PRINCIPAL DEVICE TYPES

2N3725A

2N4014

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R0 (26-August 2005)